

# HAT3015R

Silicon N/P Channel Power MOS FET  
High Speed Power Switching

REJ03G1368-0400

Rev.4.00

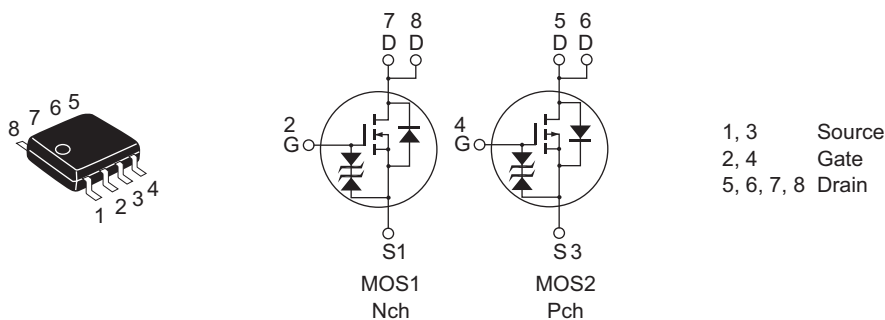
Apr 04, 2006

## Features

- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

## Outline

RENESAS Package code: PRSP0008DD-D  
(Package name: SOP-8<FP-8DAV>)



## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings		Unit
		Nch	Pch	
Drain to source voltage	V <sub>DSS</sub>	200	-200	V
Gate to source voltage	V <sub>GSS</sub>	±15	±15	V
Drain current	I <sub>D</sub>	0.5	-0.25	A
Drain peak current	I <sub>D(pulse)</sub> <sup>Note1</sup>	2	-1	A
Body-drain diode reverse drain current	I <sub>DR</sub>	0.5	-0.25	A
Channel dissipation	P <sub>ch</sub> <sup>Note2</sup>	1.3	1.3	W
	P <sub>ch</sub> <sup>Note3</sup>	2	2	W
Channel temperature	T <sub>ch</sub>	150	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1 %

2. 1 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10 s

3. 2 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10 s

## Electrical Characteristics

### • N Channel

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 15$	—	—	V	$I_G = \pm 100 \mu\text{A}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 12 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	5	$\mu\text{A}$	$V_{DS} = 200 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.1	V	$V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.6	2.2	$\Omega$	$I_D = 0.5 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>
	$R_{DS(on)}$	—	1.9	2.7	$\Omega$	$I_D = 0.5 \text{ A}$ , $V_{GS} = 4 \text{ V}$ <sup>Note4</sup>
	$R_{DS(on)}$	—	2.4	5.5	$\Omega$	$I_D = 2 \text{ A}$ , $V_{GS} = 5 \text{ V}$ <sup>Note4</sup>
Forward transfer admittance	$ y_{fs} $	0.56	0.86	—	S	$I_D = 0.5 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	120	—	pF	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	29	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	10	—	pF	
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$V_{GS} = 5 \text{ V}$ , $I_D = 0.5 \text{ A}$ , $V_{DD} \cong 30 \text{ V}$
Rise time	$t_r$	—	14	—	ns	
Turn-off delay time	$t_{d(off)}$	—	24	—	ns	
Fall time	$t_f$	—	9	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	0.9	1.4	V	$I_F = 0.5 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>

Notes: 4. Pulse test

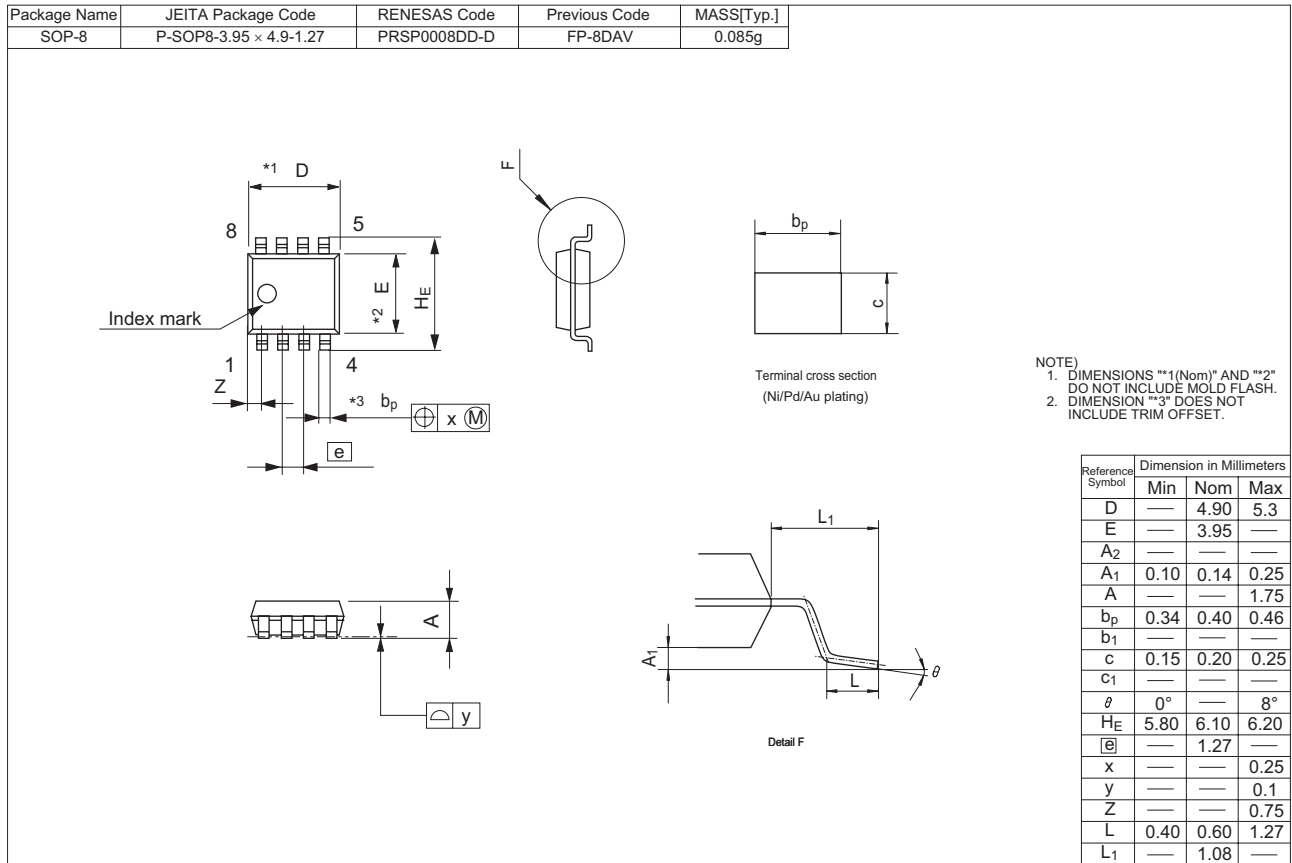
### • P Channel

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-200	—	—	V	$I_D = -10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 15$	—	—	V	$I_G = \pm 100 \mu\text{A}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 12 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-5	$\mu\text{A}$	$V_{DS} = -200 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$V_{DS} = -10 \text{ V}$ , $I_D = -1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	5.0	6.2	$\Omega$	$I_D = -0.25 \text{ A}$ , $V_{GS} = -10 \text{ V}$ <sup>Note5</sup>
	$R_{DS(on)}$	—	6.0	7.5	$\Omega$	$I_D = -0.25 \text{ A}$ , $V_{GS} = -4 \text{ V}$ <sup>Note5</sup>
	$R_{DS(on)}$	—	7.0	10.0	$\Omega$	$I_D = -1 \text{ A}$ , $V_{GS} = -5 \text{ V}$ <sup>Note5</sup>
Forward transfer admittance	$ y_{fs} $	0.29	0.45	—	S	$I_D = -0.25 \text{ A}$ , $V_{DS} = -10 \text{ V}$ <sup>Note5</sup>
Input capacitance	$C_{iss}$	—	140	—	pF	$V_{DS} = -10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	37	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	10	—	pF	
Turn-on delay time	$t_{d(on)}$	—	12	—	ns	$V_{GS} = -5 \text{ V}$ , $I_D = -0.25 \text{ A}$ , $V_{DD} \cong -30 \text{ V}$
Rise time	$t_r$	—	9	—	ns	
Turn-off delay time	$t_{d(off)}$	—	25	—	ns	
Fall time	$t_f$	—	15	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	-0.9	-1.4	V	$I_F = -0.25 \text{ A}$ , $V_{GS} = 0$ <sup>Note5</sup>

Notes: 5. Pulse test

### Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
HAT3015R-EL-E	2500 pcs	Taping

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